Abstracts

A 2.4-GHz silicon-on-sapphire CMOS low-noise amplifier

R.A. Johnson, C.E. Chang, P.R. de la Houssaye, M.E. Wood, G.A. Garcia, P.M. Asbeck and I. Lagnado. "A 2.4-GHz silicon-on-sapphire CMOS low-noise amplifier." 1997 Microwave and Guided Wave Letters 7.10 (Oct. 1997 [MGWL]): 350-352.

A low-noise amplifier operating at 2.4 GHz has been fabricated with MOSFETs in silicon-on-sapphire technology. The amplifier has a 2.8-dB noise figure, 10-dB gain, and 14-dBm output referred IP3 with 14-mW power dissipation. The amplifier was matched for minimum noise with on-chip spiral inductors and capacitors.

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